Very Low Leakage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench–based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb–Free and Halide–Free Devices

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC–DC Converters
- Freewheeling and OR-ing Diodes
- Reverse Battery Protection
- LED Lighting
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



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TRENCH SCHOTTKY RECTIFIERS **10 AMPERES 120 VOLTS**





- = Work Week
- ΖZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTS10120EMFST1G	SO–8 FL (Pb–Free)	1500 / Tape & Reel
NTS10120EMFST3G	SO–8 FL (Pb–Free)	5000 / Tape & Reel
NRVTS10120EMFST1G	SO–8 FL (Pb–Free)	1500 / Tape & Reel
NRVTS10120EMFST3G	SO–8 FL (Pb–Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	120	V	
Average Rectified Forward Current (Rated V_R , T_C = 165°C)	I _{F(AV)}	10	A	
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, T_C = 163°C)	I _{FRM}	20	A	
Non–Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	200	A	
Storage Temperature Range	T _{stg}	-65 to +175	°C	
Operating Junction Temperature	TJ	-55 to +175	°C	
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E _{AS}	100	mJ	
ESD Rating (Human Body Model)		3B		
ESD Rating (Machine Model)		M4		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)	$R_{ extsf{ heta}JC}$	1.8	-	°C/W

ELECTRICAL CHARACTERISTICS

Rating	Symbol	Тур	Мах	Unit
Instantaneous Forward Voltage (Note 1)	V _F			V
$(I_{F} = 5 \text{ A}, T_{J} = 25^{\circ}\text{C})$		0.6	-	
$(I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C})$		0.735	0.82	
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.515	-	
$(I_F = 10 \text{ A}, T_J = 125^{\circ}\text{C})$		0.588	0.63	
Instantaneous Reverse Current (Note 1)	I _R			
$(V_R = 90 V, T_J = 25^{\circ}C)$		1.0	-	μΑ
(Rated dc Voltage, $T_J = 25^{\circ}C$)		3.75	30	μΑ
$(V_R = 90 \text{ V}, \text{ T}_J = 125^{\circ}\text{C})$		2.0	-	mA
(Rated dc Voltage, $T_J = 125^{\circ}C$)		3.1	20	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = $300 \ \mu$ s, Duty Cycle $\leq 2.0\%$.

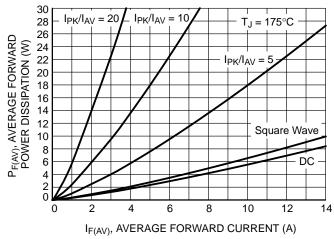
100 100 iF, INSTANTANEOUS FORWARD i_F, INSTANTANEOUS FORWARD CURRENT (A) L 01 T_A = 125°C T_A = 125°C CURRENT (A) = 150°C TΑ TA = 150°C 175°C = T_A = 175°C = 25°C = 25°C T_Α ΙA -55°C I_A = -55°C = 0.1 0.1 0.1 0.2 0.3 0.4 0.5 0.6 0.7 0.8 0.9 1.0 1.1 1.2 1.3 0.1 0.2 0.3 0.4 0.5 0.6 0.7 0.8 0.9 1.0 1.1 1.2 1.3 0 0 V_F, INSTANTANEOUS FORWARD VOLTAGE (V) V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Figure 1. Typical Instantaneous Forward Figure 2. Maximum Instantaneous Forward Characteristics Characteristics () 1.E+00 1.E-01 (¥) 1.E+00 1.E-01 1.E-02 1.E-02 1.E-03 1.E-04 1.E-05 1.E-05 1.E-07 1.E-07 T_A = 175°C 150 T_A = 175°C T_A = 125°C O III 1.E-02 III 1.E-03 III 1.E-03 III 1.E-03 III 1.E-03 III 1.E-04 III 1.E-05 III 1.E-06 T_A = 150°C T_A = 125°C T_A = 25°C T_A = 25°C 's .E-07 90 100 110 120 _ຜີ 90 100 110 120 0 20 30 40 50 60 70 80 0 10 20 30 40 50 60 70 80 10 Ŕ V_R, INSTANTANEOUS REVERSE VOLTAGE (V) V_R, INSTANTANEOUS REVERSE VOLTAGE (V) **Figure 3. Typical Reverse Characteristics Figure 4. Maximum Reverse Characteristics** I_{F(AV)}, AVERAGE FORWARD CURRENT (A) 10,000 25 T_J = 25°C $R_{\theta JC} = 1.8^{\circ}C/W$ C, JUNCTION CAPACITANCE (pF) 20 1000 DC 15 Square Wave 10 100 5 10 0 120 100 110 130 140 150 160 170 0.1 10 1 V_R, REVERSE VOLTAGE (V) T_C, CASE TEMPERATURE (°C)

TYPICAL CHARACTERISTICS

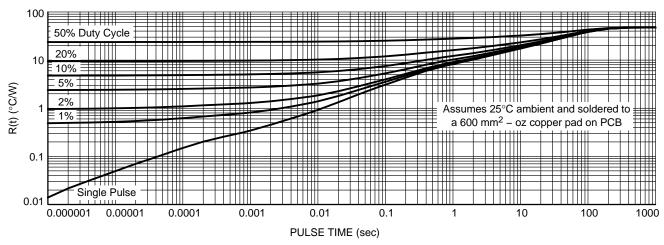
Figure 5. Typical Junction Capacitance

http://onsemi.com 3 Figure 6. Current Derating

TYPICAL CHARACTERISTICS









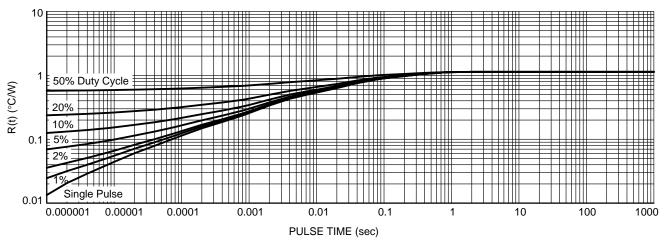
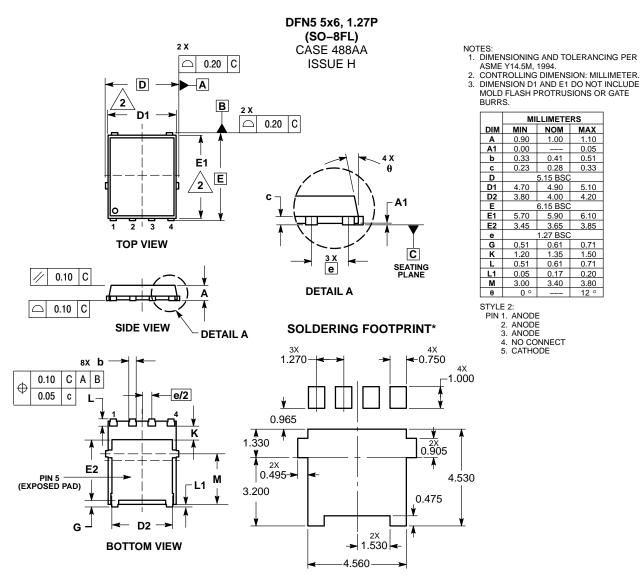


Figure 9. Typical Transient Thermal Response Characteristics, Junction-to-Case

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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